

Rev.E Mar.-2016

型号

VRW0656 M M E QSQ æ M ç s ll 1 Silicon NPN transistor in a SOT-323 Plastic Package.

参数

$S_F \approx /k_{IH} \approx h \approx \sigma B / \lambda < 348 Z$ Ȳ ´

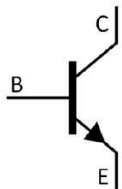
High P_C and h_{FE} , excellent h_{FE} linearity, complementary pair with 9015W.

特点

低频率 低噪声 前置放大器

Low frequency, low noise pre-amplifier.

封装与引脚



实物图



PIN1 为 Emitter

PIN 2 为 Base

PIN 3 为 Collector

性能指标

h_{FE} Classifications Symbol	A	B	C	D
h_{FE} Range	60 150	100 300	200 600	400 1000
Marking	HJ6A	HJ6B	HJ6C	HJ6D

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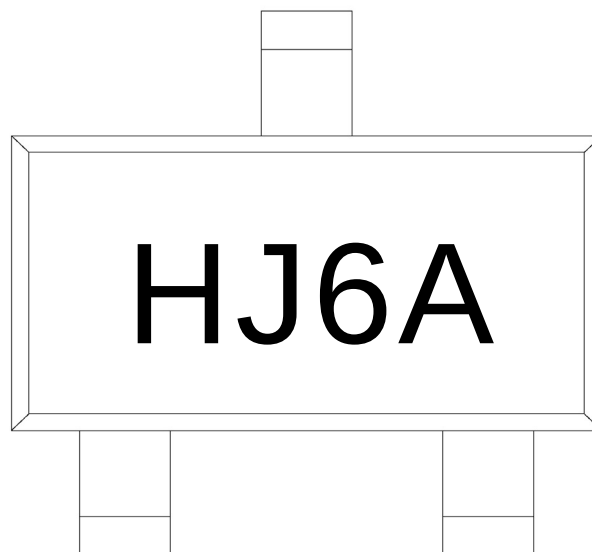
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	50	V
Collector to Emitter Voltage	V_{CEO}	45	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	250	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=0.1mA$ $I_E=0$	50			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=1.0mA$ $I_B=0$	45			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=0.1mA$ $I_C=0$	5.0			V
Collector Cut-Off Current	I					

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1. 外形



尺寸

K 尺寸

M9 尺寸

D 尺寸

Note:

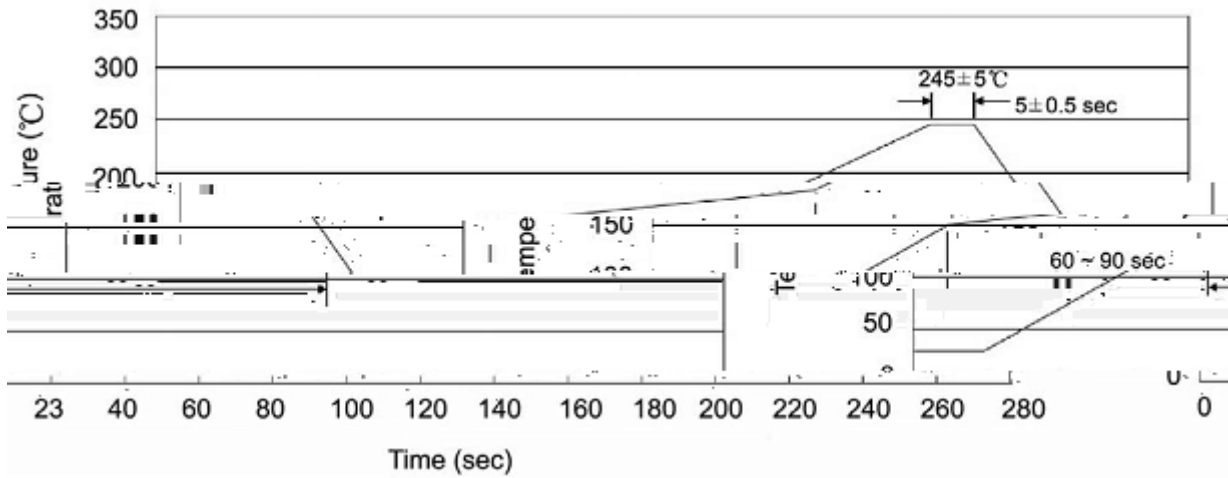
H: Company Code.

J6: Product Type.

A 尺寸 h_{FE} Classifications Symbol

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Note:

1. Preheating: 25~150 °C, Time: 60~90sec;
2. Peak Temp.: 245±5 °C, Duration: 5±0.5sec;
3. Cooling Speed: 2~10 °C/sec.

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□ ° 260±5 °C °C 10±1 sec. Temp.: 260±5 Time: 10±1 sec

9 E 2

□ ° 260±5 °C °C 10±1 sec.

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-323	3,000	10	30,000	6	180,000	7 × 8	180×120×180	390×385×205

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